

WHAT IS CLAIMED IS

1. A semiconductor device comprising:

a first insulating film formed over a semiconductor substrate;

an interconnection buried in at least a surface side of the first insulating film, and having a main interconnection portion and an extended portion provided at an end part of the main interconnection portion and extended perpendicularly to an extending direction of the main interconnection portion; and

a second insulating film formed on the first insulating film and having a contact hole down to the end part of the main interconnection portion of the interconnection.

2. A semiconductor device according to claim 1, wherein

the extended portion is extended from the end part in one direction perpendicular to the extending direction of the main interconnection portion.

3. A semiconductor device according to claim 1, wherein

the extended portion is extended from the end part in both directions perpendicular to the extending direction of the main interconnection portion.

4. A semiconductor device according to claim 1, wherein

a width of the extended portion is below a width of the

main interconnection portion.

5. A semiconductor device according to claim 1, wherein

a minimum width of the contact hole is larger than a minimum width of the interconnection.

6. A semiconductor device comprising:

a first interconnection formed over a semiconductor substrate, extended in a first direction;

a first insulating film formed over the semiconductor substrate with the first interconnection formed on;

a second interconnection buried in at least a surface side of the first insulating film, and having a main interconnection portion extended in a second direction intersecting the first direction and bridging the first interconnection and an extended portion provided at an end part of the main interconnection portion and extended in the first direction; and

a second insulating film formed on the first insulating film, and having a contact hole down to the end part of the main interconnection portion of the second interconnection.

7. A semiconductor device according to claim 6, wherein

the second interconnection is electrically connected to the first interconnection.

8. A semiconductor device according to claim 6, wherein

the second interconnection is insulated with respect to the first interconnection.

9. A method for fabricating a semiconductor device comprising the steps of:

forming an interconnection groove in a first insulating film;

burying an interconnection in the interconnection groove;

forming a second insulating film on the first insulating film with the interconnection layer buried in; and

forming a contact hole in the second insulating film down to an end part of the interconnection, in which

in the step of forming an interconnection groove, the interconnection groove is formed by using a design pattern having a main interconnection portion and an extended portion provided on an end part of the main interconnection portion and extended perpendicularly to an extending direction of the main interconnection portion.

10. A method for fabricating a semiconductor device according to claim 9, wherein

in the step of forming the interconnection groove, the interconnection groove is formed by using the design pattern having the extended portion extended from the end part in one direction perpendicular to the extending direction of the main interconnection portion.

11. A method for fabricating a semiconductor device

according to claim 9, wherein

in the step of forming an interconnection groove, the interconnection groove is formed by using the design pattern having the extended portion extended from the end part in both directions perpendicular to the extending direction of the main interconnection portion.

12. A method for fabricating a semiconductor device according to claim 9, wherein

a length of the extended portion is from 1/6 to 1/2 of a width of the main interconnection portion.

13. A method for fabricating a semiconductor device according to claim 10, wherein

a length of the extended portion is from 1/6 to 1/2 of a width of the main interconnection portion.

14. A method for fabricating a semiconductor device according to claim 11, wherein

a length of the extended portion is from 1/6 to 1/2 of a width of the main interconnection portion.

15. A method for fabricating a semiconductor device according to claim 9, wherein

a width of the extended portion is substantially equal to a width of the main interconnection portion.

16. A method for fabricating a semiconductor device according to claim 9, wherein

a minimum width of the contact hole is larger than a minimum width of the main interconnection portion.